



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

## SOT-89 Plastic-Encapsulate Transistors

**2SD2908** TRANSISTOR (NPN)

### FEATURES

Power dissipation

$P_{CM}$ : 0.5 W ( $T_{amb}=25^{\circ}C$ )

Collector current

$I_{CM}$ : 5 A

Collector-base voltage

$V_{(BR)CBO}$ : 50 V

Operating and storage junction temperature range

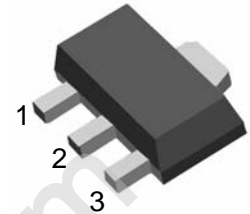
$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

### SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu A, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu A, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40V, I_E=0$			0.5	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.5	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=0.5A$	120		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=4A, I_B=100mA$			1	V
Transition frequency	$f_T$	$V_{CE}=6V, I_C=50mA, f=100MHz$		150		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=20V, I_E=0, f=1MHz$		30		pF

### CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R
Range	120-270	180-390
Marking	AHQ	AHR